

2SJ163

Silicon P-Channel Junction FET

For general switching

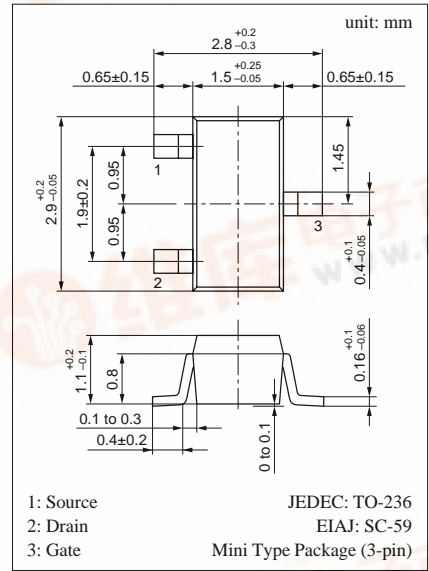
Complementary to 2SK1103

■ Features

- Low ON-resistance
- Low-noise characteristics

■ Absolute Maximum Ratings (Ta = 25°C)

Parameter	Symbol	Ratings	Unit
Gate to Drain voltage	V _{GDS}	65	V
Drain current	I _D	-20	mA
Gate current	I _G	-10	mA
Allowable power dissipation	P _D	150	mW
Channel temperature	T _{ch}	150	°C
Storage temperature	T _{stg}	-55 to +150	°C



Marking Symbol (Example): 4M

■ Electrical Characteristics (Ta = 25°C)

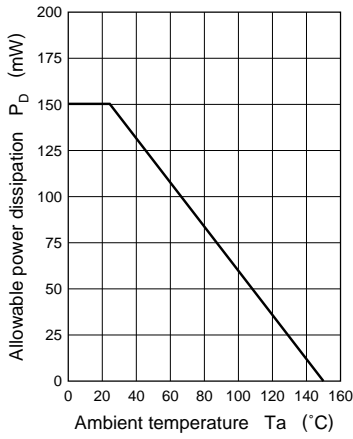
Parameter	Symbol	Conditions	min	typ	max	Unit
Drain to Source cut-off current	I _{DSS} *	V _{DS} = -10V, V _{GS} = 0	-0.2		-6	mA
Gate to Source leakage current	I _{GSS}	V _{GS} = 30V, V _{DS} = 0			10	nA
Gate to Drain voltage	V _{GDS}	I _G = 10μA, V _{DS} = 0	65			V
Gate to Source cut-off voltage	V _{GSC}	V _{DS} = -10V, I _D = -10μA		1.5	3.5	V
Forward transfer admittance	Y _{fs}	V _{DS} = -10V, I _D = -1mA, f = 1kHz	1.8	2.5		mS
Drain to Source ON-resistance	R _{DS(on)}	V _{DS} = -10mV, V _{GS} = 0		300		Ω
Input capacitance (Common Source)	C _{iss}	V _{DS} = -10V, V _{GS} = 0, f = 1MHz		12		pF
Reverse transfer capacitance (Common Source)	C _{rss}			4		pF

* I_{DSS} rank classification

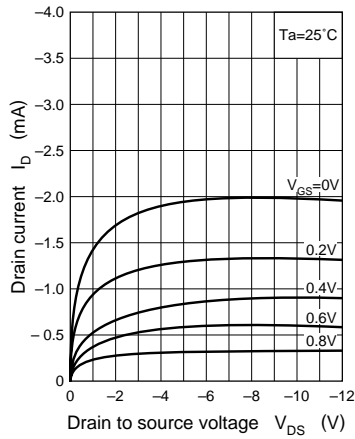
Runk	O	P	Q	R
I _{DSS} (mA)	-0.2 to -1	-0.6 to -1.5	-1 to -3	-2.5 to -6
Marking Symbol	4MO	4MP	4MQ	4MR



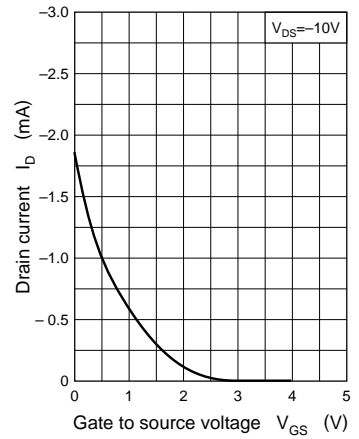
$P_D - T_a$



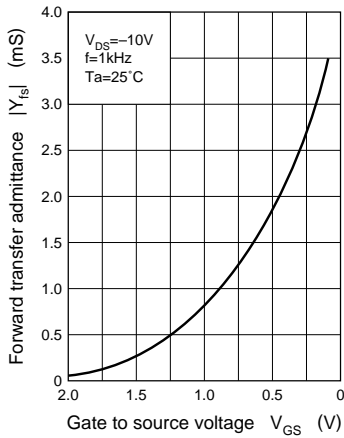
$I_D - V_{DS}$



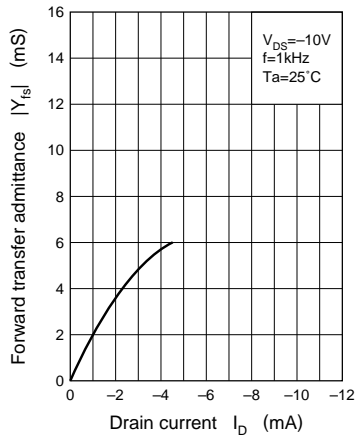
$I_D - V_{GS}$



$|Y_{fs}| - V_{GS}$



$|Y_{fs}| - I_D$



$C_{iss}, C_{oss}, C_{rss} - V_{DS}$

